

# MUN2212, MMUN2212L, MUN5212, DTC124EE, DTC124EM3, NSBC124EF3

## Digital Transistors (BRT) R1 = 22 k $\Omega$ , R2 = 22 k $\Omega$

### NPN Transistors with Monolithic Bias Resistor Network

This series of digital transistors is designed to replace a single device and its external resistor bias network. The Bias Resistor Transistor (BRT) contains a single transistor with a monolithic bias network consisting of two resistors; a series base resistor and a base-emitter resistor. The BRT eliminates these individual components by integrating them into a single device. The use of a BRT can reduce both system cost and board space.

#### Features

- Simplifies Circuit Design
- Reduces Board Space
- Reduces Component Count
- S and NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

#### MAXIMUM RATINGS (T<sub>A</sub> = 25°C)

| Rating                         | Symbol               | Max | Unit |
|--------------------------------|----------------------|-----|------|
| Collector-Base Voltage         | V <sub>CBO</sub>     | 50  | Vdc  |
| Collector-Emitter Voltage      | V <sub>CEO</sub>     | 50  | Vdc  |
| Collector Current – Continuous | I <sub>C</sub>       | 100 | mAdc |
| Input Forward Voltage          | V <sub>IN(fwd)</sub> | 40  | Vdc  |
| Input Reverse Voltage          | V <sub>IN(rev)</sub> | 10  | Vdc  |

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.



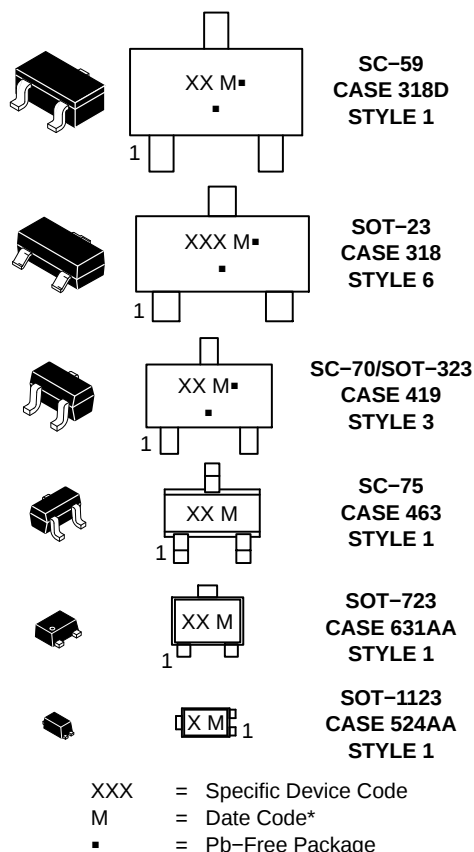
ON Semiconductor®

[www.onsemi.com](http://www.onsemi.com)

#### PIN CONNECTIONS



#### MARKING DIAGRAMS



(Note: Microdot may be in either location)

\*Date Code orientation may vary depending upon manufacturing location.

#### ORDERING INFORMATION

See detailed ordering, marking, and shipping information in the package dimensions section on page 2 of this data sheet.

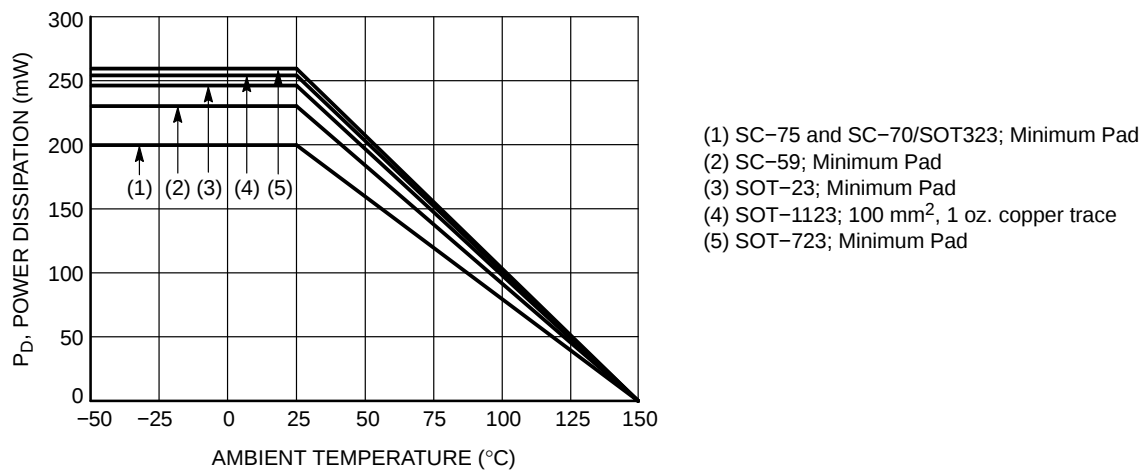
# MUN2212, MMUN2212L, MUN5212, DTC124EE, DTC124EM3, NSBC124EF3

**Table 1. ORDERING INFORMATION**

| Device                         | Part Marking | Package                   | Shipping <sup>†</sup> |
|--------------------------------|--------------|---------------------------|-----------------------|
| MUN2212T1G, NSVMUN2212T1G*     | 8B           | SC-59<br>(P-Free)         | 3000 / Tape & Reel    |
| MMUN2212LT1G, NSVMMUN2212LT1G* | A8B          | SOT-23<br>(P-Free)        | 3000 / Tape & Reel    |
| MUN5212T1G, SMUN5212T1G*       | 8B           | SC-70/SOT-323<br>(P-Free) | 3000 / Tape & Reel    |
| DTC124EET1G, SDTC124EET1G*     | 8B           | SC-75<br>(P-Free)         | 3000 / Tape & Reel    |
| DTC124EM3T5G                   | 8B           | SOT-723<br>(P-Free)       | 8000 / Tape & Reel    |
| NSBC124EF3T5G                  | L            | SOT-1123<br>(P-Free)      | 8000 / Tape & Reel    |

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

\*S and NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable.



**Figure 1. Derating Curve**

Table 2. THERMAL CHARACTERISTICS

| Characteristic | Symbol | Max | Unit |
|----------------|--------|-----|------|
|----------------|--------|-----|------|

**THERMAL CHARACTERISTICS (SC-59) (MUN2212)**

|                                                                                                                  |                                   |                          |             |
|------------------------------------------------------------------------------------------------------------------|-----------------------------------|--------------------------|-------------|
| Total Device Dissipation<br>T <sub>A</sub> = 25°C (Note 1)<br>(Note 2)<br>Derate above 25°C (Note 1)<br>(Note 2) | P <sub>D</sub>                    | 230<br>338<br>1.8<br>2.7 | mW<br>mW/°C |
| Thermal Resistance,<br>Junction to Ambient (Note 1)<br>(Note 2)                                                  | R <sub>θJA</sub>                  | 540<br>370               | °C/W        |
| Thermal Resistance,<br>Junction to Lead (Note 1)<br>(Note 2)                                                     | R <sub>θJL</sub>                  | 264<br>287               | °C/W        |
| Junction and Storage Temperature Range                                                                           | T <sub>J</sub> , T <sub>stg</sub> | -55 to +150              | °C          |

**THERMAL CHARACTERISTICS (SOT-23) (MMUN2212L)**

|                                                                                                                  |                                   |                          |             |
|------------------------------------------------------------------------------------------------------------------|-----------------------------------|--------------------------|-------------|
| Total Device Dissipation<br>T <sub>A</sub> = 25°C (Note 1)<br>(Note 2)<br>Derate above 25°C (Note 1)<br>(Note 2) | P <sub>D</sub>                    | 246<br>400<br>2.0<br>3.2 | mW<br>mW/°C |
| Thermal Resistance,<br>Junction to Ambient (Note 1)<br>(Note 2)                                                  | R <sub>θJA</sub>                  | 508<br>311               | °C/W        |
| Thermal Resistance,<br>Junction to Lead (Note 1)<br>(Note 2)                                                     | R <sub>θJL</sub>                  | 174<br>208               | °C/W        |
| Junction and Storage Temperature Range                                                                           | T <sub>J</sub> , T <sub>stg</sub> | -55 to +150              | °C          |

**THERMAL CHARACTERISTICS (SC-70/SOT-323) (MUN5212)**

|                                                                                                                  |                                   |                          |             |
|------------------------------------------------------------------------------------------------------------------|-----------------------------------|--------------------------|-------------|
| Total Device Dissipation<br>T <sub>A</sub> = 25°C (Note 1)<br>(Note 2)<br>Derate above 25°C (Note 1)<br>(Note 2) | P <sub>D</sub>                    | 202<br>310<br>1.6<br>2.5 | mW<br>mW/°C |
| Thermal Resistance,<br>Junction to Ambient (Note 1)<br>(Note 2)                                                  | R <sub>θJA</sub>                  | 618<br>403               | °C/W        |
| Thermal Resistance,<br>Junction to Lead (Note 1)<br>(Note 2)                                                     | R <sub>θJL</sub>                  | 280<br>332               | °C/W        |
| Junction and Storage Temperature Range                                                                           | T <sub>J</sub> , T <sub>stg</sub> | -55 to +150              | °C          |

**THERMAL CHARACTERISTICS (SC-75) (DTC124EE)**

|                                                                                                                  |                                   |                          |             |
|------------------------------------------------------------------------------------------------------------------|-----------------------------------|--------------------------|-------------|
| Total Device Dissipation<br>T <sub>A</sub> = 25°C (Note 1)<br>(Note 2)<br>Derate above 25°C (Note 1)<br>(Note 2) | P <sub>D</sub>                    | 200<br>300<br>1.6<br>2.4 | mW<br>mW/°C |
| Thermal Resistance,<br>Junction to Ambient (Note 1)<br>(Note 2)                                                  | R <sub>θJA</sub>                  | 600<br>400               | °C/W        |
| Junction and Storage Temperature Range                                                                           | T <sub>J</sub> , T <sub>stg</sub> | -55 to +150              | °C          |

**THERMAL CHARACTERISTICS (SOT-723) (DTC124EM3)**

|                                                                                                                  |                                   |                          |             |
|------------------------------------------------------------------------------------------------------------------|-----------------------------------|--------------------------|-------------|
| Total Device Dissipation<br>T <sub>A</sub> = 25°C (Note 1)<br>(Note 2)<br>Derate above 25°C (Note 1)<br>(Note 2) | P <sub>D</sub>                    | 260<br>600<br>2.0<br>4.8 | mW<br>mW/°C |
| Thermal Resistance,<br>Junction to Ambient (Note 1)<br>(Note 2)                                                  | R <sub>θJA</sub>                  | 480<br>205               | °C/W        |
| Junction and Storage Temperature Range                                                                           | T <sub>J</sub> , T <sub>stg</sub> | -55 to +150              | °C          |

1. FR-4 @ Minimum Pad.
2. FR-4 @ 1.0 x 1.0 Inch Pad.
3. FR-4 @ 100 mm<sup>2</sup>, 1 oz. copper traces, still air.
4. FR-4 @ 500 mm<sup>2</sup>, 1 oz. copper traces, still air.

**Table 2. THERMAL CHARACTERISTICS**

| Characteristic                                                                                                   | Symbol                            | Max                      | Unit        |
|------------------------------------------------------------------------------------------------------------------|-----------------------------------|--------------------------|-------------|
| <b>THERMAL CHARACTERISTICS (SOT-1123) (NSBC124EF3)</b>                                                           |                                   |                          |             |
| Total Device Dissipation<br>T <sub>A</sub> = 25°C (Note 3)<br>(Note 4)<br>Derate above 25°C (Note 3)<br>(Note 4) | P <sub>D</sub>                    | 254<br>297<br>2.0<br>2.4 | mW<br>mW/°C |
| Thermal Resistance, Junction to Ambient<br>(Note 3)<br>(Note 4)                                                  | R <sub>θJA</sub>                  | 493<br>421               | °C/W        |
| Thermal Resistance, Junction to Lead<br>(Note 3)                                                                 | R <sub>θJL</sub>                  | 193                      | °C/W        |
| Junction and Storage Temperature Range                                                                           | T <sub>J</sub> , T <sub>stg</sub> | -55 to +150              | °C          |

1. FR-4 @ Minimum Pad.
2. FR-4 @ 1.0 x 1.0 Inch Pad.
3. FR-4 @ 100 mm<sup>2</sup>, 1 oz. copper traces, still air.
4. FR-4 @ 500 mm<sup>2</sup>, 1 oz. copper traces, still air.

**Table 3. ELECTRICAL CHARACTERISTICS** (T<sub>A</sub> = 25°C, unless otherwise noted)

| Characteristic                                                                                     | Symbol                         | Min  | Typ | Max  | Unit |
|----------------------------------------------------------------------------------------------------|--------------------------------|------|-----|------|------|
| <b>OFF CHARACTERISTICS</b>                                                                         |                                |      |     |      |      |
| Collector-Base Cutoff Current<br>(V <sub>CB</sub> = 50 V, I <sub>E</sub> = 0)                      | I <sub>CBO</sub>               | –    | –   | 100  | nAdc |
| Collector-Emitter Cutoff Current<br>(V <sub>CE</sub> = 50 V, I <sub>B</sub> = 0)                   | I <sub>CEO</sub>               | –    | –   | 500  | nAdc |
| Emitter-Base Cutoff Current<br>(V <sub>EB</sub> = 6.0 V, I <sub>C</sub> = 0)                       | I <sub>EBO</sub>               | –    | –   | 0.2  | mAdc |
| Collector-Base Breakdown Voltage<br>(I <sub>C</sub> = 10 μA, I <sub>E</sub> = 0)                   | V <sub>(BR)CBO</sub>           | 50   | –   | –    | Vdc  |
| Collector-Emitter Breakdown Voltage (Note 5)<br>(I <sub>C</sub> = 2.0 mA, I <sub>B</sub> = 0)      | V <sub>(BR)CEO</sub>           | 50   | –   | –    | Vdc  |
| <b>ON CHARACTERISTICS</b>                                                                          |                                |      |     |      |      |
| DC Current Gain (Note 5)<br>(I <sub>C</sub> = 5.0 mA, V <sub>CE</sub> = 10 V)                      | h <sub>FE</sub>                | 60   | 100 | –    |      |
| Collector-Emitter Saturation Voltage (Note 5)<br>(I <sub>C</sub> = 10 mA, I <sub>B</sub> = 0.3 mA) | V <sub>CE(sat)</sub>           | –    | –   | 0.25 | Vdc  |
| Input Voltage (off)<br>(V <sub>CE</sub> = 5.0 V, I <sub>C</sub> = 100 μA)                          | V <sub>i(off)</sub>            | –    | 1.2 | 0.8  | Vdc  |
| Input Voltage (on)<br>(V <sub>CE</sub> = 0.3 V, I <sub>C</sub> = 5.0 mA)                           | V <sub>i(on)</sub>             | 2.5  | 1.6 | –    | Vdc  |
| Output Voltage (on)<br>(V <sub>CC</sub> = 5.0 V, V <sub>B</sub> = 2.5 V, R <sub>L</sub> = 1.0 kΩ)  | V <sub>OL</sub>                | –    | –   | 0.2  | Vdc  |
| Output Voltage (off)<br>(V <sub>CC</sub> = 5.0 V, V <sub>B</sub> = 0.5 V, R <sub>L</sub> = 1.0 kΩ) | V <sub>OH</sub>                | 4.9  | –   | –    | Vdc  |
| Input Resistor                                                                                     | R <sub>1</sub>                 | 15.4 | 22  | 28.6 | kΩ   |
| Resistor Ratio                                                                                     | R <sub>1</sub> /R <sub>2</sub> | 0.8  | 1.0 | 1.2  |      |

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

5. Pulsed Condition: Pulse Width = 300 msec, Duty Cycle ≤ 2%.

TYPICAL CHARACTERISTICS  
MUN2212, MMUN2212L, NSVMMUN2212LT1G, MUN5212, DTC124EE, DTC124EM3

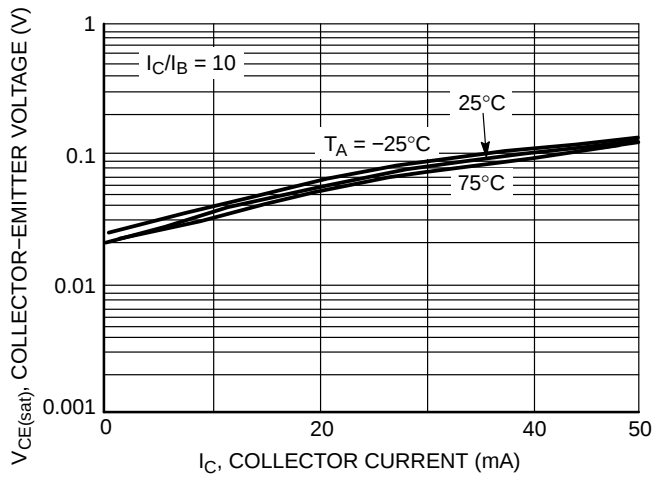


Figure 2.  $V_{CE(sat)}$  vs.  $I_C$

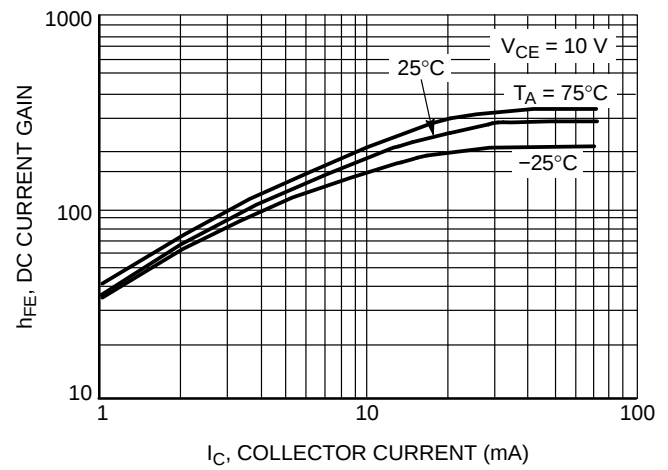


Figure 3. DC Current Gain

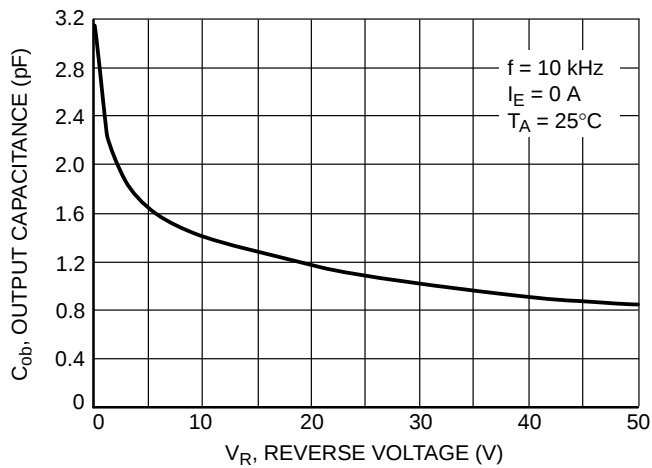


Figure 4. Output Capacitance

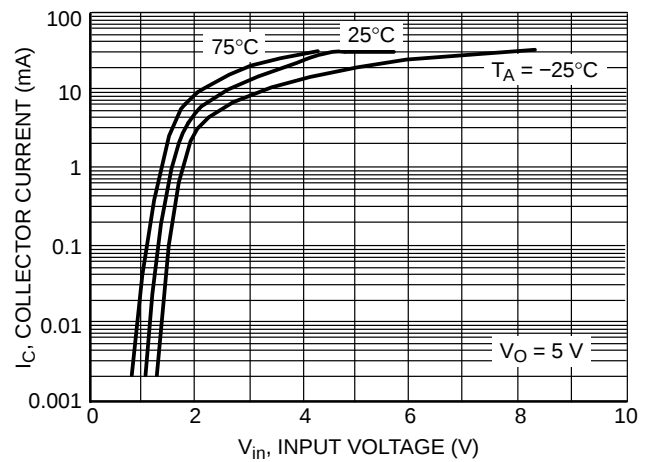


Figure 5. Output Current vs. Input Voltage

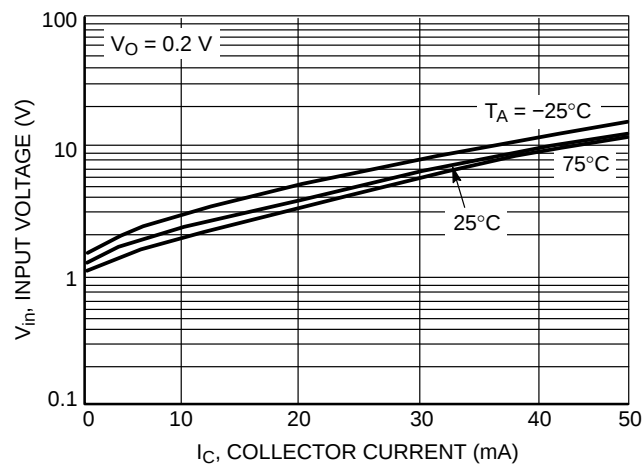


Figure 6. Input Voltage vs. Output Current

TYPICAL CHARACTERISTICS – NSBC124EF3

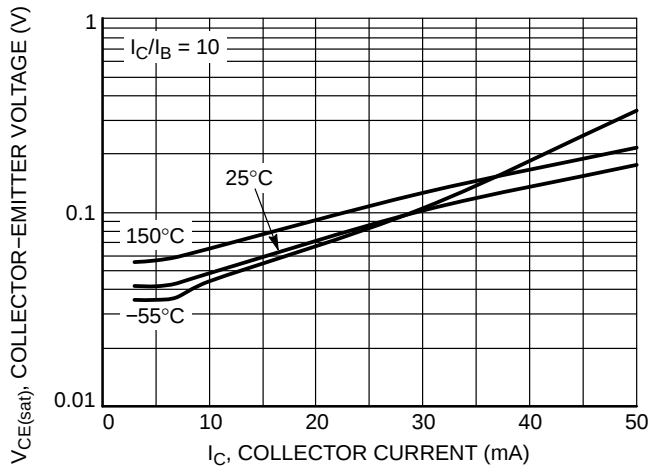


Figure 7.  $V_{CE(sat)}$  vs.  $I_C$

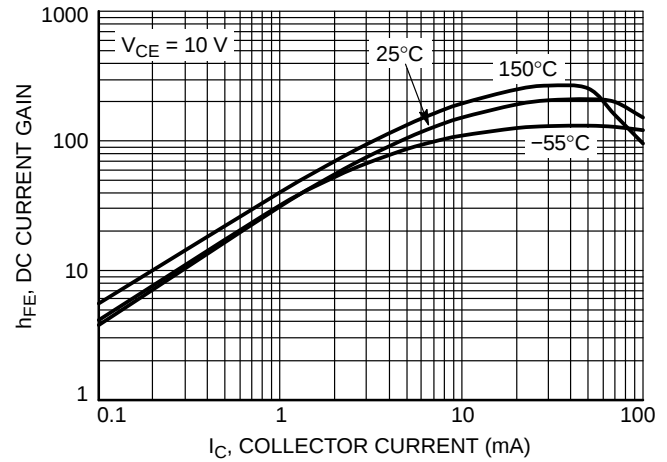


Figure 8. DC Current Gain

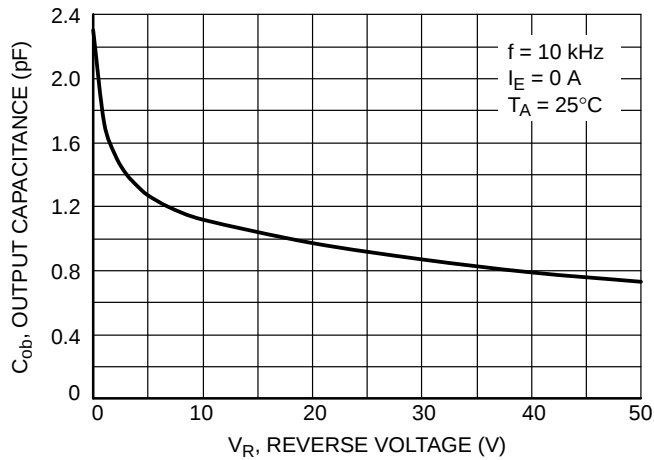


Figure 9. Output Capacitance

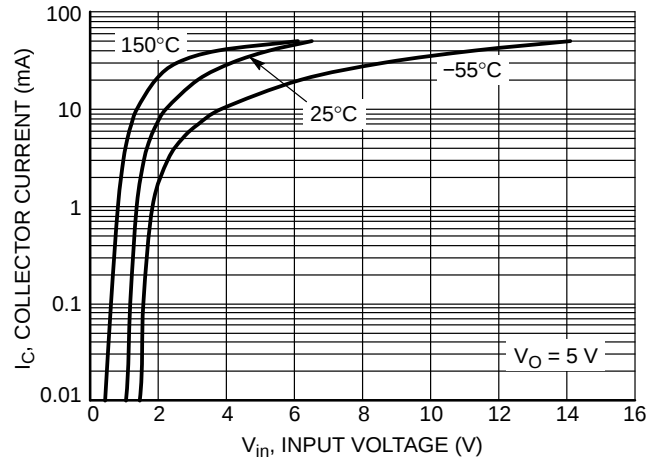


Figure 10. Output Current vs. Input Voltage

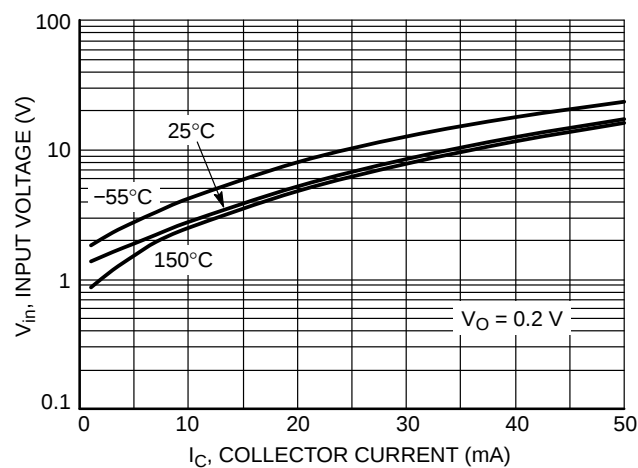
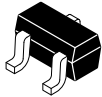


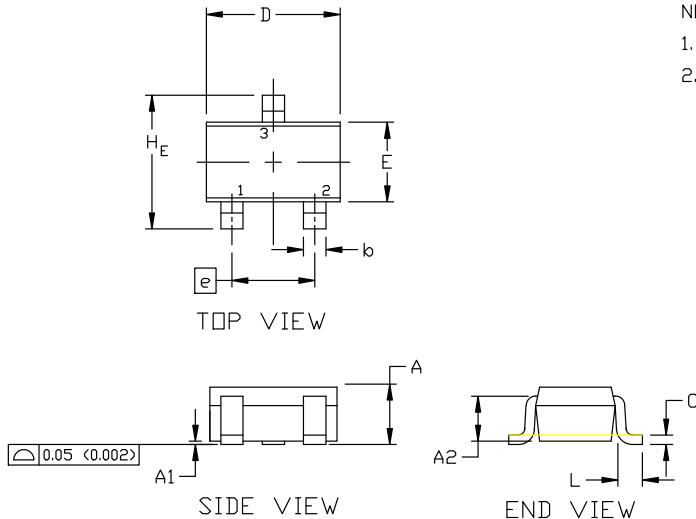
Figure 11. Input Voltage vs. Output Current



SCALE 4:1

SC-70 (SOT-323)  
CASE 419  
ISSUE R

DATE 11 OCT 2022

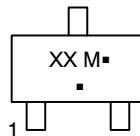


NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH

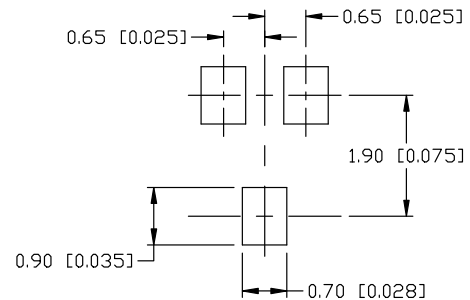
| DIM            | MILLIMETERS |      |      | INCHES    |       |       |
|----------------|-------------|------|------|-----------|-------|-------|
|                | MIN.        | NOM. | MAX. | MIN.      | NOM.  | MAX.  |
| A              | 0.80        | 0.90 | 1.00 | 0.032     | 0.035 | 0.040 |
| A1             | 0.00        | 0.05 | 0.10 | 0.000     | 0.002 | 0.004 |
| A2             | 0.70 REF    |      |      | 0.028 BSC |       |       |
| b              | 0.30        | 0.35 | 0.40 | 0.012     | 0.014 | 0.016 |
| c              | 0.10        | 0.18 | 0.25 | 0.004     | 0.007 | 0.010 |
| D              | 1.80        | 2.00 | 2.20 | 0.071     | 0.080 | 0.087 |
| E              | 1.15        | 1.24 | 1.35 | 0.045     | 0.049 | 0.053 |
| e              | 1.20        | 1.30 | 1.40 | 0.047     | 0.051 | 0.055 |
| e1             | 0.65 BSC    |      |      | 0.026 BSC |       |       |
| L              | 0.20        | 0.38 | 0.56 | 0.008     | 0.015 | 0.022 |
| H <sub>E</sub> | 2.00        | 2.10 | 2.40 | 0.079     | 0.083 | 0.095 |

GENERIC  
MARKING DIAGRAM



XX = Specific Device Code  
M = Date Code  
▪ = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.



\* For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

SOLDERING FOOTPRINT

STYLE 1:  
CANCELLED

STYLE 2:  
PIN 1. ANODE  
2. N.C.  
3. CATHODE

STYLE 3:  
PIN 1. BASE  
2. EMITTER  
3. COLLECTOR

STYLE 4:  
PIN 1. CATHODE  
2. CATHODE  
3. ANODE

STYLE 5:  
PIN 1. ANODE  
2. ANODE  
3. CATHODE

STYLE 6:  
PIN 1. EMITTER  
2. BASE  
3. COLLECTOR

STYLE 7:  
PIN 1. BASE  
2. EMITTER  
3. COLLECTOR

STYLE 8:  
PIN 1. GATE  
2. SOURCE  
3. DRAIN

STYLE 9:  
PIN 1. ANODE  
2. CATHODE  
3. CATHODE-ANODE

STYLE 10:  
PIN 1. CATHODE  
2. ANODE  
3. ANODE-CATHODE

STYLE 11:  
PIN 1. CATHODE  
2. CATHODE  
3. CATHODE

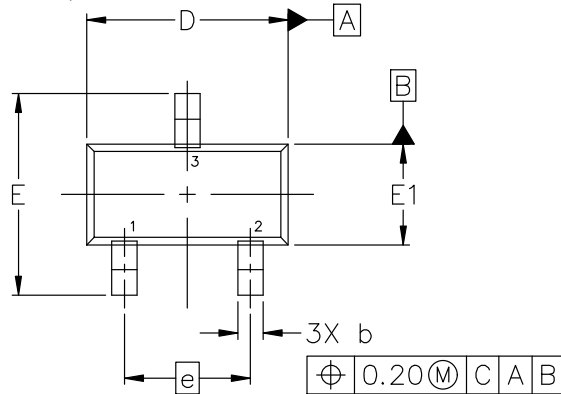
|                  |                 |                                                                                                                                                                                     |
|------------------|-----------------|-------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|
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| DESCRIPTION:     | SC-70 (SOT-323) | PAGE 1 OF 1                                                                                                                                                                         |

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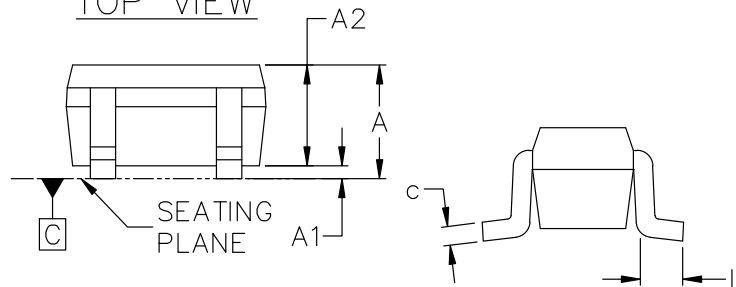
**SC75-3 1.60x0.80x0.80, 1.00P**

CASE 463  
ISSUE H

DATE 01 FEB 2024



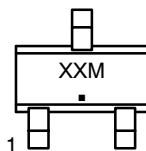
TOP VIEW



SIDE VIEW

END VIEW

**GENERIC MARKING DIAGRAM\***



XX = Specific Device Code  
M = Date Code  
▪ = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

STYLE 1:  
PIN 1. BASE  
2. EMITTER  
3. COLLECTOR

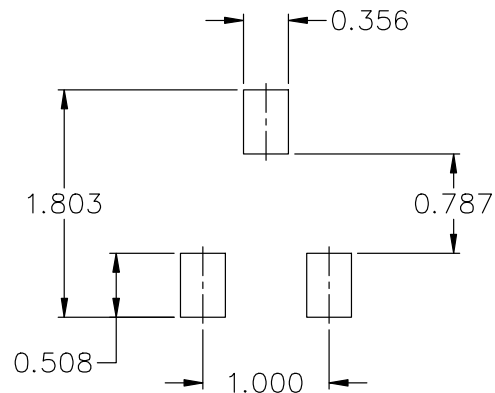
STYLE 2:  
PIN 1. ANODE  
2. N/C  
3. CATHODE

STYLE 3:  
PIN 1. ANODE  
2. ANODE  
3. CATHODE

STYLE 4:  
PIN 1. CATHODE  
2. CATHODE  
3. ANODE

STYLE 5:  
PIN 1. GATE  
2. SOURCE  
3. DRAIN

| DIM | MILLIMETERS |      |      |
|-----|-------------|------|------|
|     | MIN.        | NOM. | MAX. |
| A   | 0.70        | 0.80 | 0.90 |
| A1  | 0.00        | 0.05 | 0.10 |
| A2  | 0.80 REF.   |      |      |
| b   | 0.15        | 0.20 | 0.30 |
| c   | 0.10        | 0.15 | 0.25 |
| D   | 1.55        | 1.60 | 1.65 |
| E   | 1.50        | 1.60 | 1.70 |
| E1  | 0.70        | 0.80 | 0.90 |
| e   | 1.00 BSC    |      |      |
| L   | 0.10        | 0.15 | 0.20 |

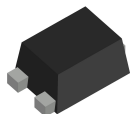


**RECOMMENDED MOUNTING FOOTPRINT\***

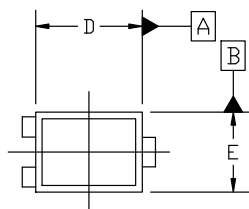
\* FOR ADDITIONAL INFORMATION ON OUR Pb-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ON SEMICONDUCTOR SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D.

|                         |                                     |                                                                                                                                                                                  |
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| <b>DESCRIPTION:</b>     | <b>SC75-3 1.60x0.80x0.80, 1.00P</b> | <b>PAGE 1 OF 1</b>                                                                                                                                                               |

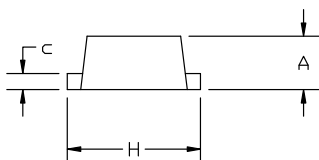
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**SOT-1123 0.80x0.60x0.37, 0.35P**  
**CASE 524AA**  
**ISSUE D**

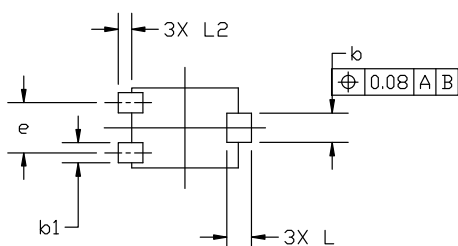
DATE 18 JAN 2024



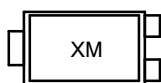
TOP VIEW



SIDE VIEW



BOTTOM VIEW

**GENERIC**  
**MARKING DIAGRAM\***

X = Specific Device Code  
M = Date Code

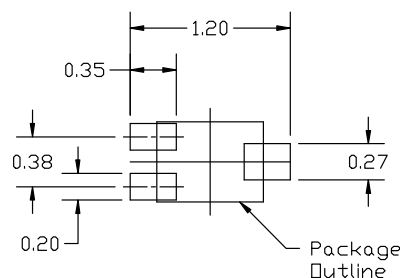
\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

## NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2018.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

## MILLIMETERS

| DIM | MIN       | NOM   | MAX   |
|-----|-----------|-------|-------|
| A   | 0.34      | 0.37  | 0.40  |
| b   | 0.15      | 0.22  | 0.28  |
| b1  | 0.10      | 0.15  | 0.20  |
| c   | 0.07      | 0.12  | 0.17  |
| D   | 0.75      | 0.80  | 0.85  |
| E   | 0.55      | 0.60  | 0.65  |
| e   | 0.35      | 0.38  | 0.40  |
| H   | 0.950     | 1.000 | 1.050 |
| L   | 0.185 REF |       |       |
| L2  | 0.05      | 0.10  | 0.15  |


**RECOMMENDED**  
**MOUNTING FOOTPRINT**

\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference manual, SOLDERM/D.

STYLE 1:  
PIN 1. BASE  
2. EMITTER  
3. COLLECTOR

STYLE 2:  
PIN 1. ANODE  
2. N/C  
3. CATHODE

STYLE 3:  
PIN 1. ANODE  
2. ANODE  
3. CATHODE

STYLE 4:  
PIN 1. CATHODE  
2. CATHODE  
3. ANODE

STYLE 5:  
PIN 1. GATE  
2. SOURCE  
3. DRAIN

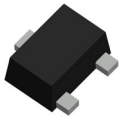
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**DESCRIPTION:** SOT-1123 0.80x0.60x0.37, 0.35P

**PAGE 1 OF 1**

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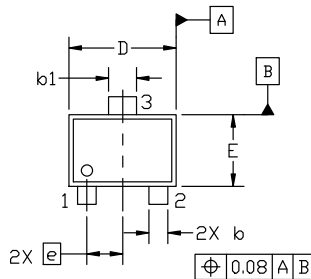


**SOT-723 1.20x0.80x0.50, 0.40P**  
**CASE 631AA**  
**ISSUE E**

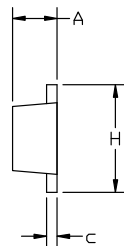
DATE 24 JAN 2024

NOTES:

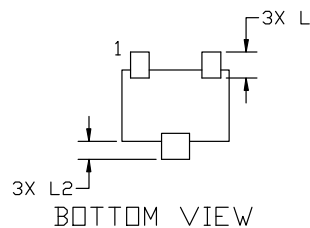
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2018.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.



TOP VIEW

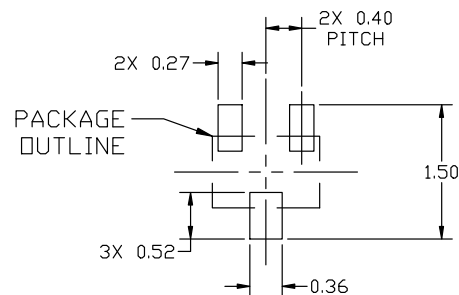


SIDE VIEW



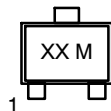
BOTTOM VIEW

| DIM | MILLIMETERS |      |      |
|-----|-------------|------|------|
|     | MIN.        | NOM. | MAX. |
| A   | 0.45        | 0.50 | 0.55 |
| b   | 0.15        | 0.21 | 0.27 |
| b1  | 0.25        | 0.31 | 0.37 |
| c   | 0.07        | 0.12 | 0.17 |
| D   | 1.15        | 1.20 | 1.25 |
| E   | 0.75        | 0.80 | 0.85 |
| e   | 0.40 BSC    |      |      |
| H   | 1.15        | 1.20 | 1.25 |
| L   | 0.29 REF    |      |      |
| L2  | 0.15        | 0.20 | 0.25 |



RECOMMENDED MOUNTING  
FOOTPRINT

**GENERIC  
MARKING DIAGRAM\***



XX = Specific Device Code  
M = Date Code

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERM/D.

|                                                       |                                                  |                                                    |                                                      |                                                  |
|-------------------------------------------------------|--------------------------------------------------|----------------------------------------------------|------------------------------------------------------|--------------------------------------------------|
| STYLE 1:<br>PIN 1. BASE<br>2. EMITTER<br>3. COLLECTOR | STYLE 2:<br>PIN 1. ANODE<br>2. N/C<br>3. CATHODE | STYLE 3:<br>PIN 1. ANODE<br>2. ANODE<br>3. CATHODE | STYLE 4:<br>PIN 1. CATHODE<br>2. CATHODE<br>3. ANODE | STYLE 5:<br>PIN 1. GATE<br>2. SOURCE<br>3. DRAIN |
|-------------------------------------------------------|--------------------------------------------------|----------------------------------------------------|------------------------------------------------------|--------------------------------------------------|

|                         |                                      |                                                                                                                                                                                  |
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| <b>DESCRIPTION:</b>     | <b>SOT-723 1.20x0.80x0.50, 0.40P</b> | <b>PAGE 1 OF 1</b>                                                                                                                                                               |

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